

1200V N-Channel MOSFET
Description

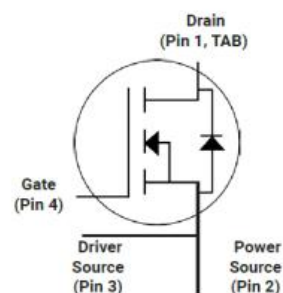
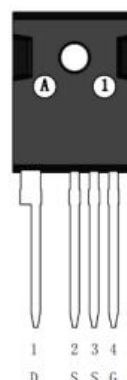
Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Optimized package with separate driver source pin
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free

Application

- EV motor drive
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Solar inverters
- EV charging


Ordering Information

Part Number	Marking	Package	Packaging
ASC200N1200MT4	ASC200N1200MT4	TO-247-4	Tube

Absolute Maximum Ratings(Tc=25℃)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	1200	V
I_D	Drain Current(continuous)at Tc=25℃	200	A
I_D	Drain Current(continuous)at Tc=100℃	165	A
I_{DM}	Drain Current (pulsed)	385	A
V_{GS}	Gate-Source Voltage	-10/+22V	V
P_D	Power Dissipation T _C = 25℃	681	W
T _J , Tstg	Junction and Storage Temperature Range	-55 to +175	℃

Electrical Characteristics(T_J = 25℃ unless otherwise specified)
Typical Performance-Static

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain-source Breakdown Voltage	$I_D=250\mu A, V_{GS}=0V$	1200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1200V,$ $V_{GS}=0V, T_J=25^\circ C$		10	150	μA
I_{GSS}	Gate-body Leakage Current	$V_{DS}=0V ; V_{GS}=-10$ to 20V		20	300	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=30mA$	2	3	4	V
$V_{GS(on)}$	Recommended turn-on Voltage	Static		18		V
$V_{GS(off)}$	Recommended turn-off Voltage			-5		V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS}=18V, I_D=100A$		7.5	9	mΩ
		$V_{GS}=18V, I_D=100A$ $T_J=175^\circ C$		12		mΩ

Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=1000V, f=1MHz,$ $V_{AC}=25mV$		14		nF
C_{oss}	Output Capacitance			568		pF
C_{rss}	Reverse Transfer Capacitance			158		pF
g_{fs}	Transconductance	$V_{DS}=20V, I_D=100A$		68		S
E_{oss}	C_{oss} Stored Energy	$V_{DS}=1000V, f=1MHz$		285		μJ
E_{ON}	Turn-On Energy (Body Diode)	$V_{DS}=800V,$ $V_{GS}=-5/18V, I_D=100A,$ $L=68\mu H$		5.8		mJ
E_{OFF}	Turn-Off Energy (Body Diode)			3.1		mJ
Q_g	Total Gate Charge	$V_{DS}=800V,$ $V_{GS}=-5V/18V, I_D=100A$		415		nC
Q_{gs}	Gate-source Charge			152		nC
Q_{gd}	Gate-Drain Charge			156		nC
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		1.1		Ω
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=800V,$ $V_{GS}=-5V/18V,$ $I_D=100A, L=68\mu H$ $R_{ext}=2.5\Omega$		60		ns
t_r	Rise Time			75		ns
$t_{d(off)}$	Turn-off Delay Time			108		ns
t_f	Fall Time			27		ns

Typical Performance-Reverse Diode($T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FSD}	Forward Voltage	$V_{GS}=0V, I_F=70A, T_J=25^\circ C$		3.3	6	V
		$V_{GS}=0V, I_F=70A, T_J=175^\circ C$		3.1	6	V
I_S	Continuous Diode Forward Current	$V_{GS}=0V, T_C=25^\circ C$		180		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-5V, I_F=70A,$ $V_R=800V, di/dt=1200A/\mu s,$ $T_J=175^\circ C$		115		nS
Q_{rr}	Reverse Recovery Charge			1235		nC
I_{rrm}	Peak Reverse Recovery Current			30		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.22	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^\circ C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of $T_J(max)=175^\circ C$

Electrical Characteristics

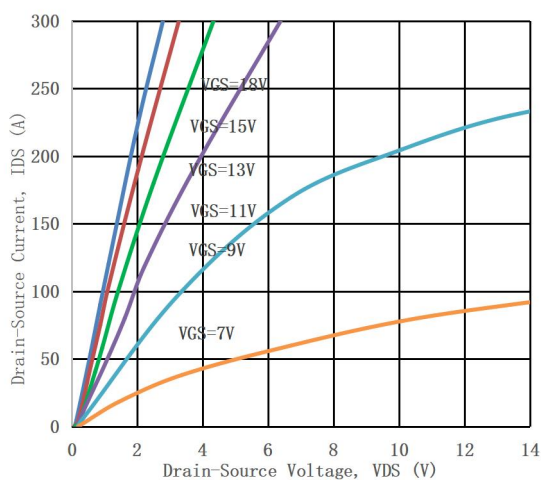
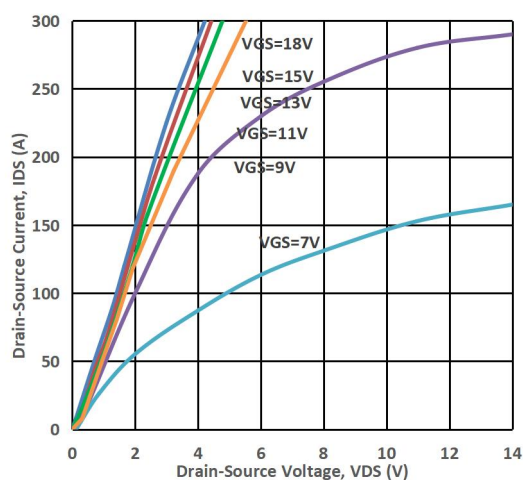
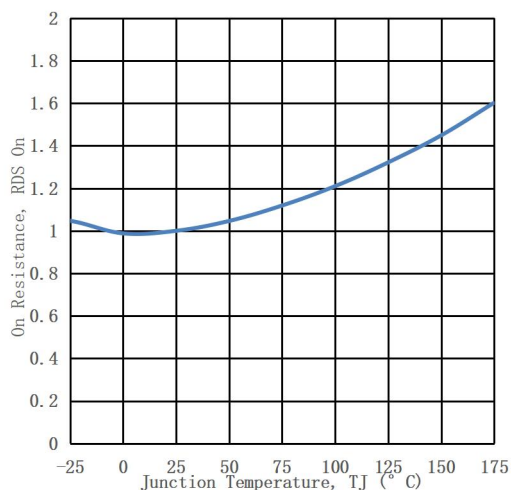
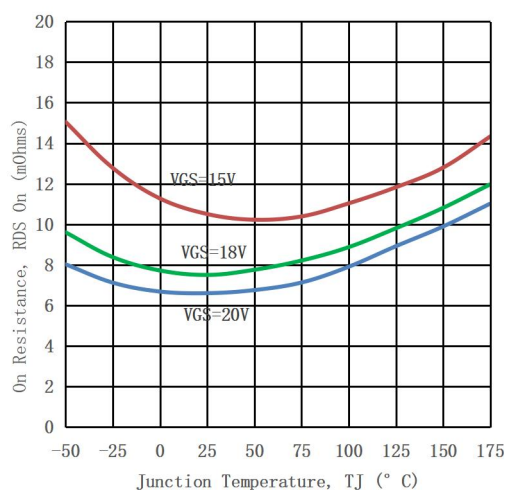
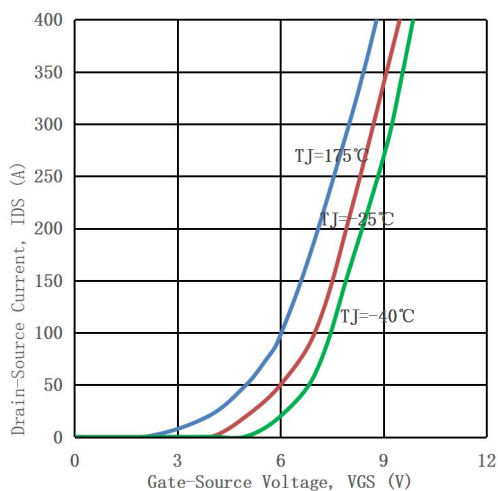
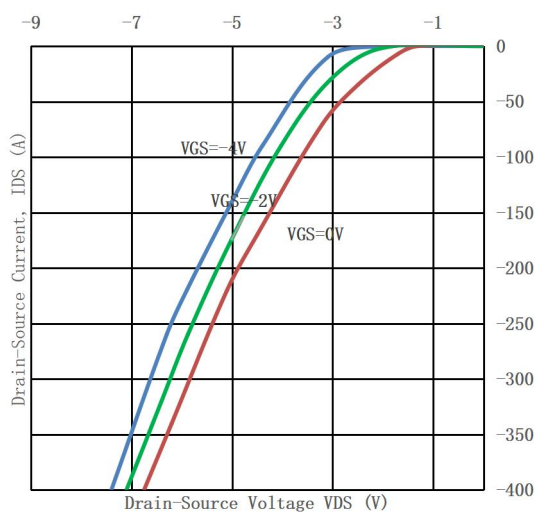
Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

Fig2. Output characteristics ($T_J = 175^\circ\text{C}$)

Fig3. Normalized On-Resistance vs. Temperature

Fig4. On-Resistance vs. Temperature

Fig5. Transfer Characteristic

Fig6. Body Diode Characteristic at 25°C


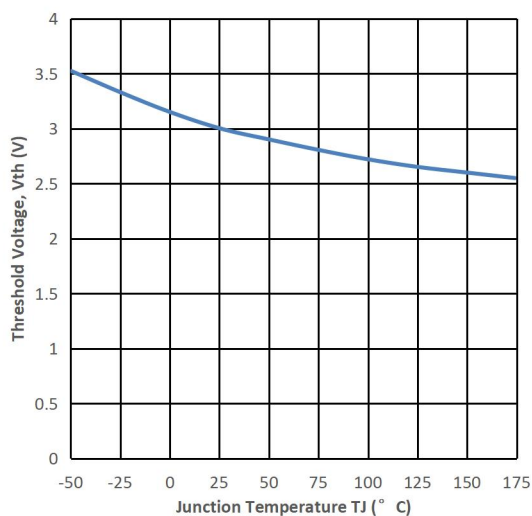
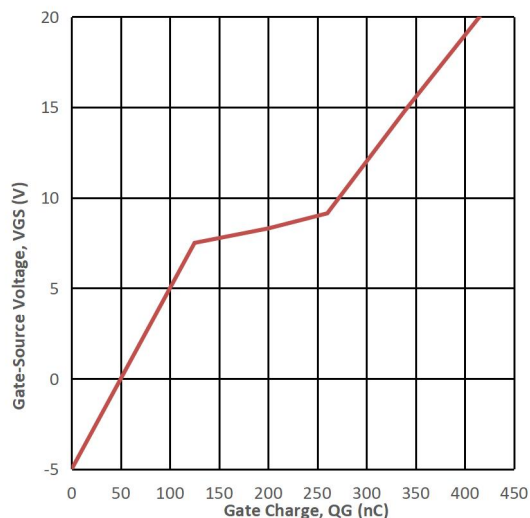
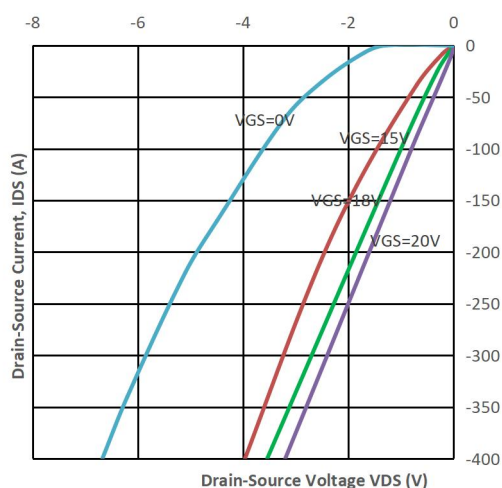
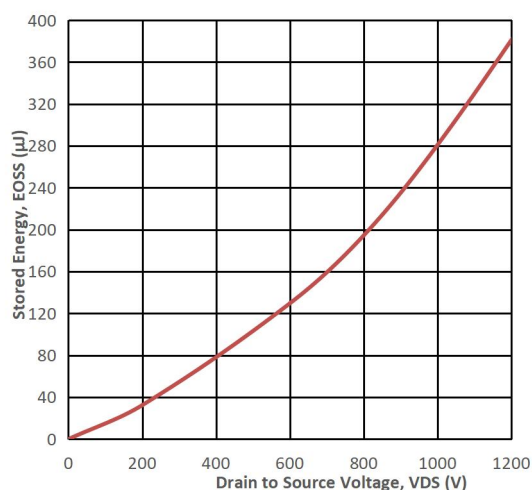
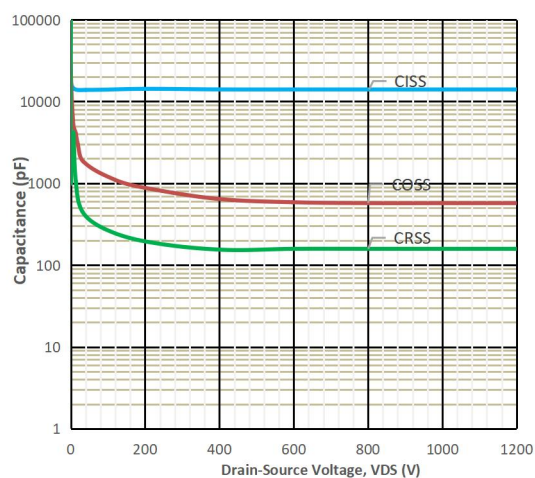
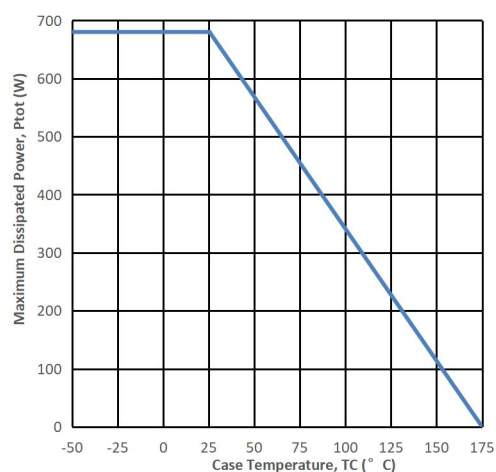
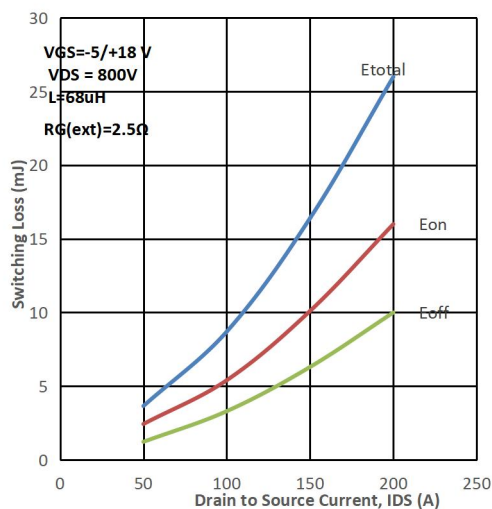
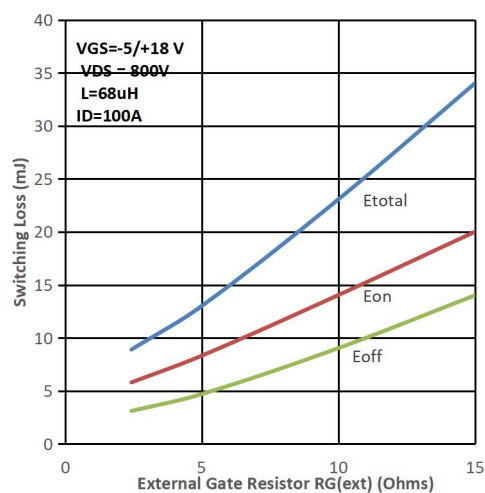
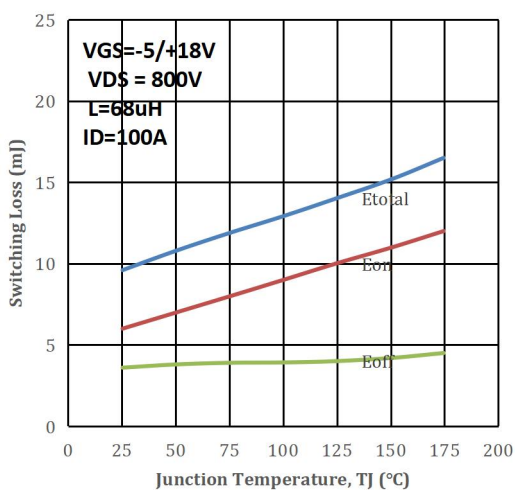
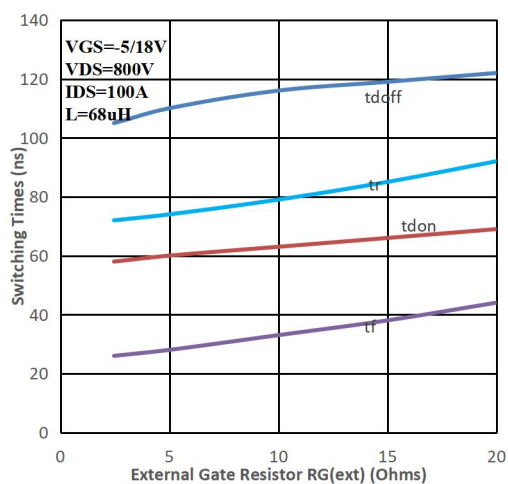
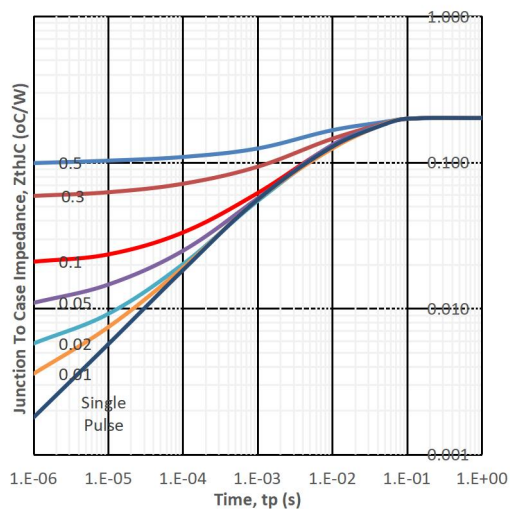
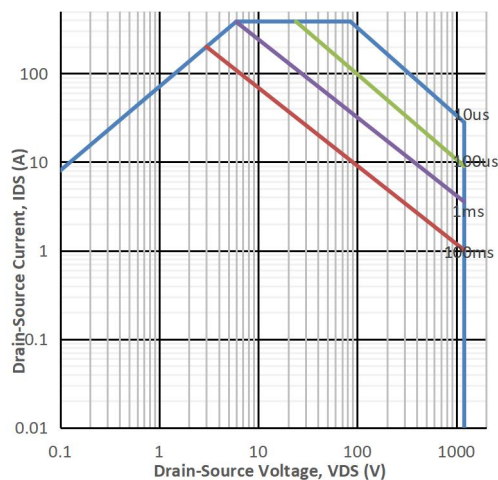
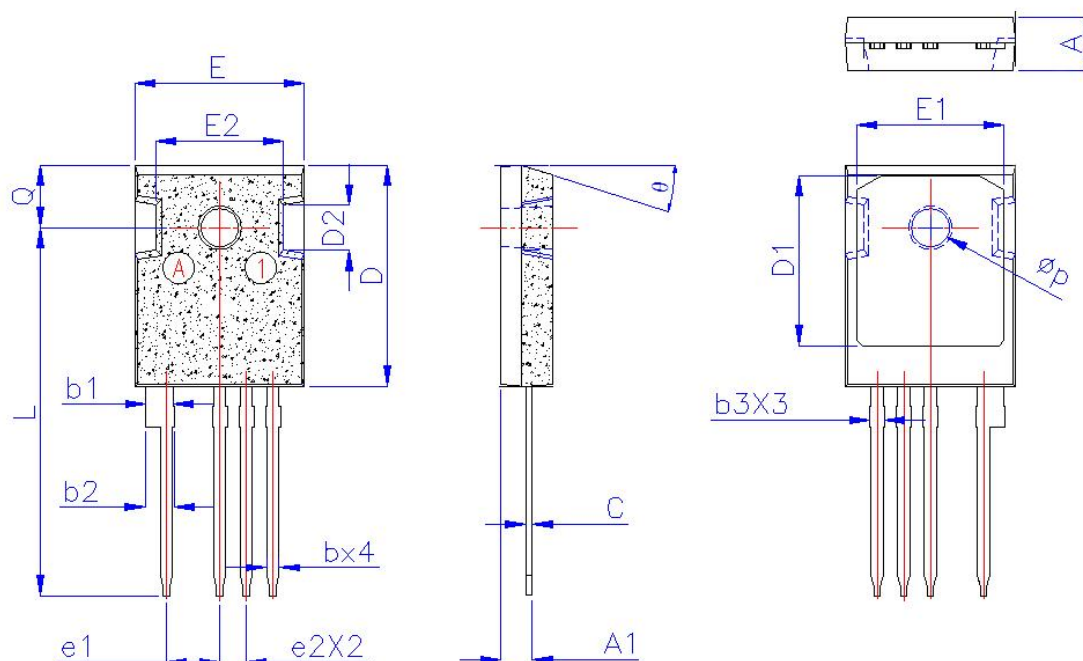
Fig7. Threshold Voltage vs. Temperature

Fig8. Gate Charge Characteristics

Fig9. 3rd Quadrant Characteristic at 25 °C

Fig10. Output Capacitor Stored Energy

Fig11. Capacitances vs. Drain-Source

Fig12. Max Power Dissipation Derating Vs Tc


Fig13. Switching Energy vs. Drain Current

Fig14. Switching Energy vs. RG(ext)

Fig15. Switching Energy vs. Temperature

Fig16. Switching Times vs. RG(ext)

Fig17. Transient Thermal Impedance

Fig18. Safe Operating Area


Package Drawing:

Dimensions (UNIT: mm)

SYMBDLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	TYPE	MAX	MIN	TYPE	MAX
A	4.80	5.00	5.20	0.189	0.197	0.205
A1	2.85	3.00	3.15	0.112	0.118	0.124
b	1.15	1.20	1.25	0.045	0.047	0.049
b1	2.40	2.50	2.60	0.094	0.098	0.102
b2	2.61	2.76	2.91	0.103	0.109	0.115
b3	1.30	1.42	1.57	0.051	0.056	0.062
C	0.55	0.60	0.65	0.022	0.024	0.026
D	20.80	21.00	21.20	0.819	0.827	0.835
D1	15.94	16.24	16.54	0.628	0.639	0.651
D2	4.3TYPE			0.169TYPE		
e1	4.93	5.08	5.23	0.194	0.200	0.206
e2	2.39	2.54	2.69	0.094	0.100	0.106
E	15.95	16.15	16.35	0.628	0.636	0.644
E1	13.82	14.02	14.26	0.544	0.552	0.561
E2	12.00	12.20	12.40	0.472	0.480	0.488
L	34.65	35.05	35.45	1.364	1.380	1.396
Q	5.85	5.95	6.05	0.230	0.234	0.238
øP	3.45	3.60	3.75	0.136	0.142	0.148
θ	17.5°			0.689°		

Notes:

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